

Emitter common (dual transistors)

EMY1 / UMY1N / FMY1A

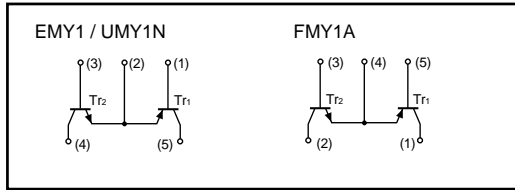
●Features

- 1) Includes a 2SA1037AK and a 2SC2412K transistor in a EMT or UMT or SMT package.
- 2) PNP and NPN transistors have common emitters.
- 3) Mounting cost and area can be cut in half.

●Structure

Epitaxial planar type
PNP / NPN silicon transistor

●Equivalent circuit

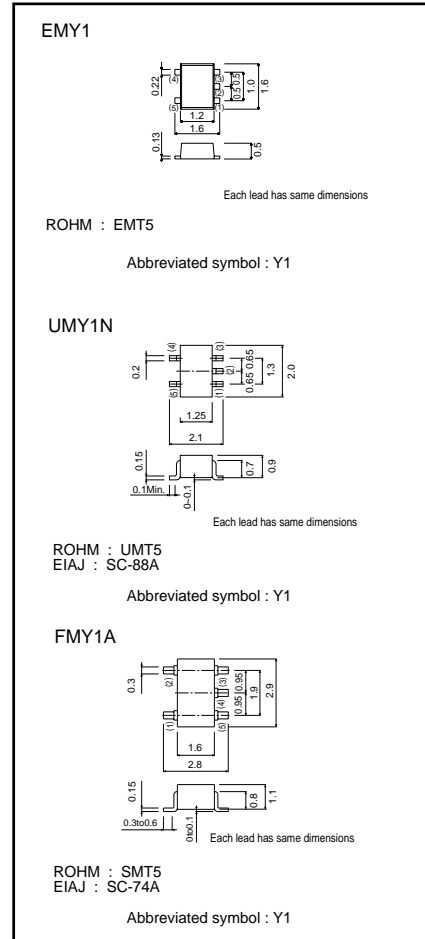


●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits		Unit
		Tr1	Tr2	
Collector-base voltage	V _{CB0}	-60	60	V
Collector-emitter voltage	V _{CE0}	-50	50	V
Emitter-base voltage	V _{EB0}	-6	7	V
Collector current	I _c	-150	150	mA
Power dissipation	EMY1, UMY1N	150 (TOTAL) ^{*1}		mW
	FMY1A	300 (TOTAL) ^{*2}		
Junction temperature	T _j	150		°C
Storage temperature	T _{stg}	-55 to +150		°C

*1 120mW per element must not be exceeded.
*2 200mW per element must not be exceeded.

●External dimensions (Unit : mm)



Transistors

●Electrical characteristics (Ta = 25°C)

Tr1 (PNP)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	-60	-	-	V	I _C =-50μA
Collector-emitter breakdown voltage	BV _{CEO}	-50	-	-	V	I _C =-1mA
Emitter-base breakdown voltage	BV _{EBO}	-6	-	-	V	I _E =-50μA
Collector cutoff current	I _{CBO}	-	-	-0.1	μA	V _{CB} =-60V
Emitter cutoff current	I _{EBO}	-	-	-0.1	μA	V _{EB} =-6V
Collector-emitter saturation voltage	V _{CE(sat)}	-	-	-0.5	V	I _C /I _B =-50mA/-5mA
DC current transfer ratio	h _{FE}	120	-	560	-	V _{CE} =-6V, I _C =-1mA
Transition frequency	f _T	-	140	-	MHz	V _{CE} =-12V, I _E =2mA, f=100MHz
Output capacitance	C _{ob}	-	4	5	PF	V _{CB} =-12V, I _E =0A, f=1MHz

Tr2 (NPN)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	60	-	-	V	I _C =50μA
Collector-emitter breakdown voltage	BV _{CEO}	50	-	-	V	I _C =1mA
Emitter-base breakdown voltage	BV _{EBO}	7	-	-	V	I _E =50μA
Collector cutoff current	I _{CBO}	-	-	0.1	μA	V _{CB} =60V
Emitter cutoff current	I _{EBO}	-	-	0.1	μA	V _{EB} =7V
Collector-emitter saturation voltage	V _{CE(sat)}	-	-	0.4	V	I _C /I _B =50mA/5mA
DC current transfer ratio	h _{FE}	120	-	560	-	V _{CE} =6V, I _C =1mA
Transition frequency	f _T	-	180	-	MHz	V _{CE} =12V, I _E =-2mA, f=100MHz
Output capacitance	C _{ob}	-	2	3.5	PF	V _{CB} =12V, I _E =0A, f=1MHz

●Packaging specifications

Type	Packaging type	Taping		
	Code	T2R	TR	T148
	Basic ordering unit (pieces)	8000	3000	3000
EMY1	○	—	—	—
UMY1N	—	○	—	—
FMY1	—	—	—	○

●Electrical characteristic curves

Tr1 (PNP)

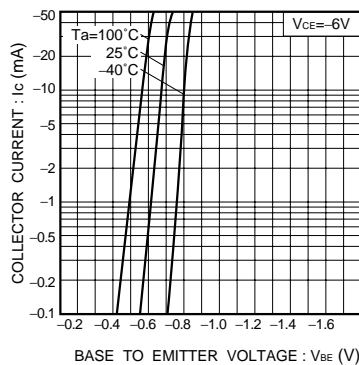


Fig.1 Grounded emitter propagation characteristics

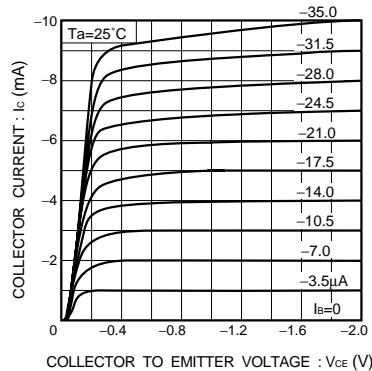


Fig.2 Grounded emitter output characteristics (I)

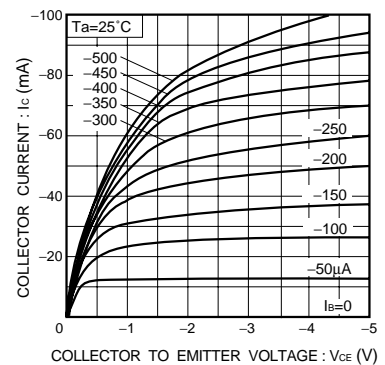


Fig.3 Grounded emitter output characteristics (II)

Transistors

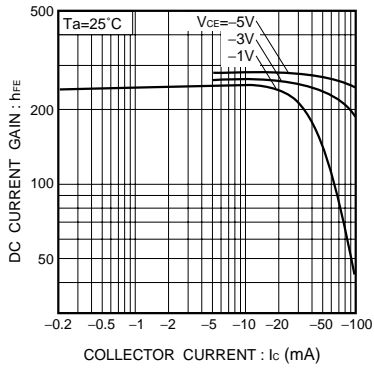


Fig.4 DC current gain vs. collector current (I)

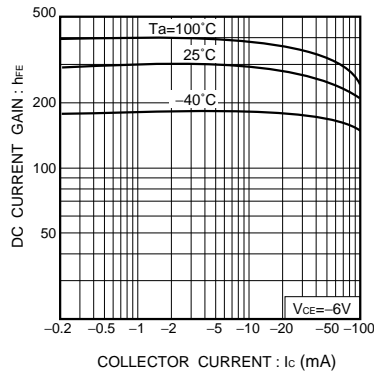


Fig.5 DC current gain vs. collector current (II)

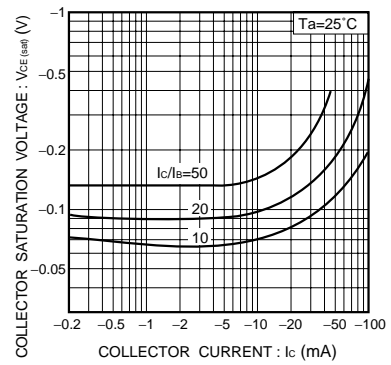


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

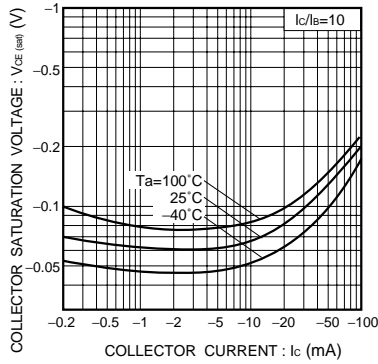


Fig.7 Collector-emitter saturation voltage vs. collector current (II)

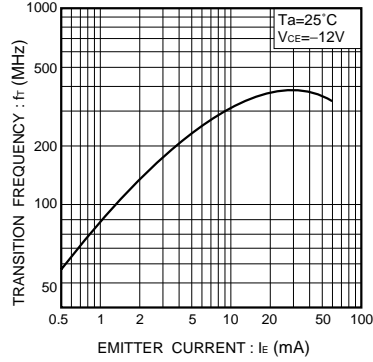


Fig.8 Gain bandwidth product vs. emitter current

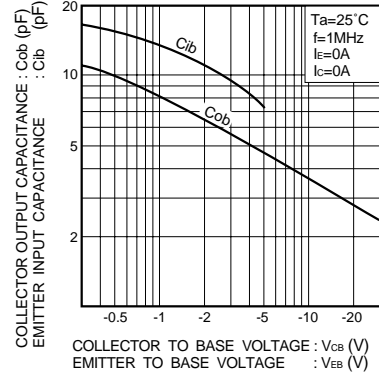


Fig.9 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

T_{r2} (NPN)

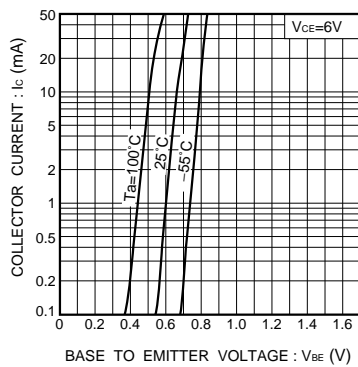


Fig.10 Grounded emitter propagation characteristics

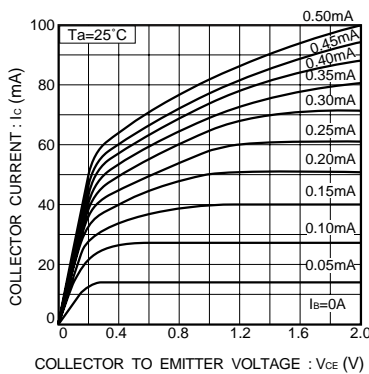


Fig.11 Grounded emitter output characteristics (I)

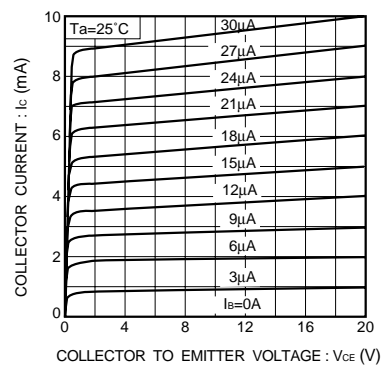


Fig.12 Grounded emitter output characteristics (II)

Transistors

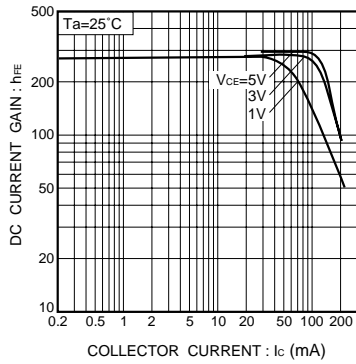


Fig.13 DC current gain vs. collector current (I)

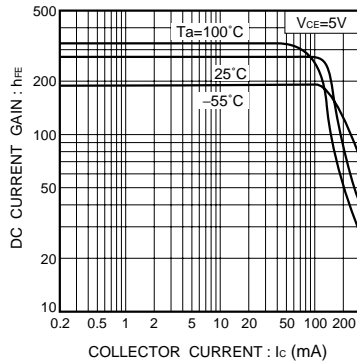


Fig.14 DC current gain vs. collector current (II)

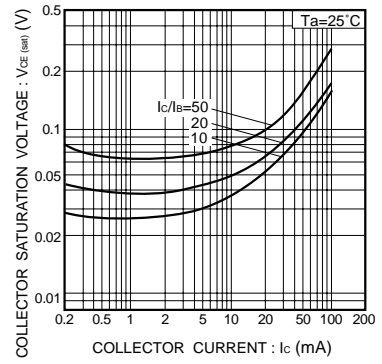


Fig.15 Collector-emitter saturation voltage vs. collector current (I)

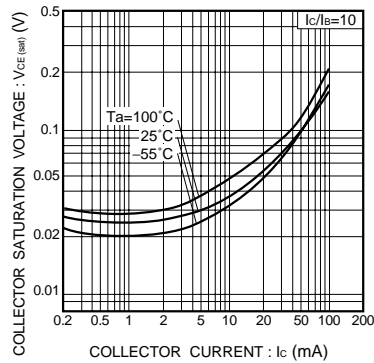


Fig.16 Collector-emitter saturation voltage vs. collector current (II)

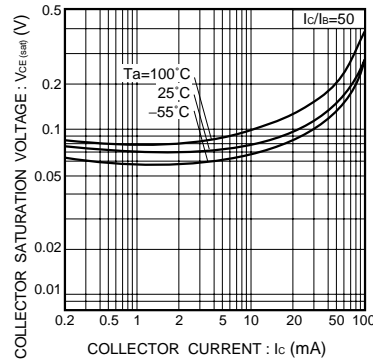


Fig.17 Collector-emitter saturation voltage vs. collector current (III)

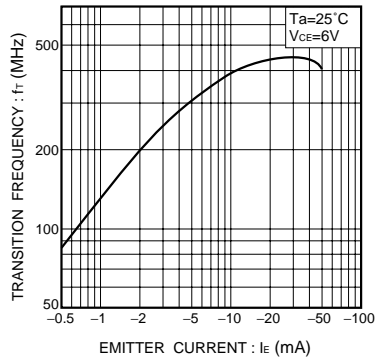


Fig.18 Gain bandwidth product vs. emitter current

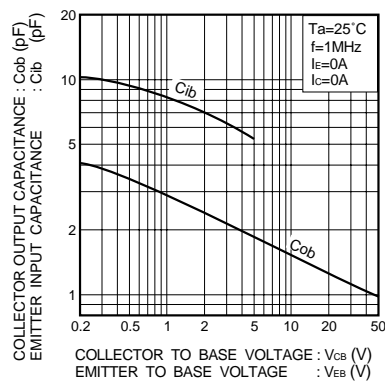


Fig.19 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

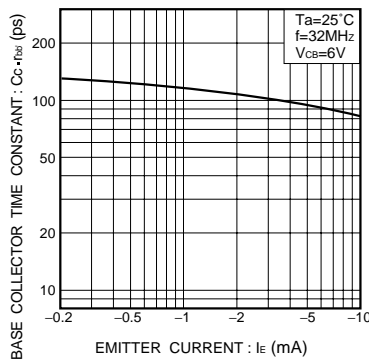


Fig.20 Base-collector time constant vs. emitter current

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